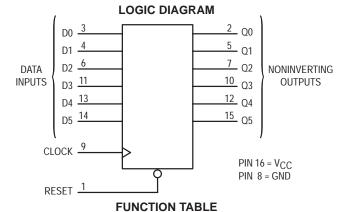
Hex D Flip-Flop with Common Clock and Reset

High-Performance Silicon-Gate CMOS

The MC74HC174A is identical in pinout to the LS174. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

This device consists of six D flip-flops with common Clock and Reset inputs. Each flip-flop is loaded with a low-to-high transition of the Clock input. Reset is asynchronous and active-low.

- Output Drive Capability: 10 LSTTL Loads
- TTL NMOS Compatible Input Levels
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 4.5 to 5.5 V
- Low Input Current: 1.0 μA
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 162 FETs or 40.5 Equivalent Gates



	Inputs		Output
Reset	Clock	D	Q
L	Х	Χ	L
Н	\mathcal{L}	Н	Н
Н	_	L	L
Н	L	X	No Change
Н	$\overline{}$	Χ	No Change

Design Criteria	Value	Units
Internal Gate Count*	40.5	ea.
Internal Gate Propagation Delay	1.5	ns
Internal Gate Power Dissipation	5.0	μW
Speed Power Product	.0075	рJ

^{*}Equivalent to a two-input NAND gate.



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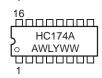


PDIP-16 N SUFFIX CASE 648





SO-16 D SUFFIX CASE 751B



A = Assembly Location

WL = Wafer Lot YY = Year WW = Work Week

PIN ASSIGNMENT

RESET [1 •	16	v _{cc}
Q0 [2	15] Q5
D0 [3	14] D5
D1 [4	13	D4
Q1 [5	12] Q4
D2 [6	11] D3
Q2 [7	10] Q3
GND [8	9	CLOCK

ORDERING INFORMATION

Device	Package	Shipping
MC74HC174AN	PDIP-16	2000 / Box
MC74HC174AD	SOIC-16	48 / Rail
MC74HC174ADR2	SOIC-16	2500 / Reel

MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
VCC	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	- 1.5 to V _{CC} + 1.5	V
V _{out}	DC Output Voltage (Referenced to GND)	-0.5 to V _{CC} + 0.5	V
lin	DC Input Current, per Pin	± 20	mA
l _{out}	DC Output Current, per Pin	± 25	mA
ICC	DC Supply Current, V _{CC} and GND Pins	± 50	mA
PD	Power Dissipation in Still Air, Plastic DIP† SOIC Package†	750 500	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP or SOIC Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq VCC. Unused inputs must always be tied to an appropriate logic voltage

level (e.g., either GND or V_{CC}). Unused outputs must be left open.

SOIC Package: - 7 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
VCC	DC Supply Voltage (Referenced to GND)			6.0	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)			Vcc	V
TA	Operating Temperature, All Package Types			+ 125	°C
t _r , t _f	Input Rise and Fall Time (Figure 1)	V _{CC} = 2.0 V V _{CC} = 4.5 V V _{CC} = 6.0 V	0 0 0	1000 500 400	ns

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	V _C C	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
V _{IH}	Minimum High-Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$	2.0 4.5 6.0	1.5 3.15 4.2	1.5 3.15 4.2	1.5 3.15 4.2	V
VIL	Maximum Low–Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$	2.0 4.5 6.0	0.5 1.35 1.8	0.5 1.35 1.8	0.5 1.35 1.8	V
VOH	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \ \mu\text{A}$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$V_{\text{in}} = V_{\text{IH}} \text{ or } V_{\text{IL}}$ $ I_{\text{out}} \le 4.0 \text{ mA}$ $ I_{\text{out}} \le 5.2 \text{ mA}$	4.5 6.0	3.98 5.48	3.84 5.34	3.7 5.2	
VOL	Maximum Low–Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \mu\text{A}$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$V_{\text{in}} = V_{\text{IH}} \text{ or } V_{\text{IL}}$ $ I_{\text{out}} \le 4.0 \text{ mA}$ $ I_{\text{out}} \le 5.2 \text{ mA}$	4.5 6.0	0.26 0.26	0.33 0.33	0.4 0.4	

^{*}Maximum Ratings are those values beyond which damage to the device may occur.

Functional operation should be restricted to the Recommended Operating Conditions.

[†]Derating — Plastic DIP: – 10 mW/°C from 65° to 125°C

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu			
Symbol	Parameter	Test Conditions	V _{CC}	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
l _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	6.0	± 0.1	± 1.0	± 1.0	μΑ
Icc	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	6.0	4.0	40	160	μА

NOTES:

- 1. Information on typical parametric values along with high frequency or heavy load considerations, can be found in Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).
- 2. Total Supply Current = $I_{CC} + S\Delta I_{CC}$.

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_f = t_f = 6.0 \text{ ns}$)

			Gu	Guaranteed Limit		
Symbol	Parameter	V _{CC}	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
f _{max}	Maximum Clock Frequency (50% Duty Cycle) (Figures 1 and 4)	2.0 4.5 6.0	6.0 30 35	4.8 24 28	4.0 20 24	MHz
^t PLH ^t PHL	Maximum Propagation Delay, Clock to Q (Figures 1 and 4)	2.0 4.5 6.0	110 22 19	140 28 24	165 33 28	ns
^t PLH ^t PHL	Maximum Propagation Delay, Reset to Q (Figures 2 and 4)		110 21 19	140 28 24	160 32 27	ns
tTLH tTHL	Maximum Output Transition Time, Any Output (Figures 1 and 4)	2.0 4.5 6.0	75 15 13	95 19 16	110 22 19	ns
C _{in}	Maximum Input Capacitance		10	10	10	pF

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

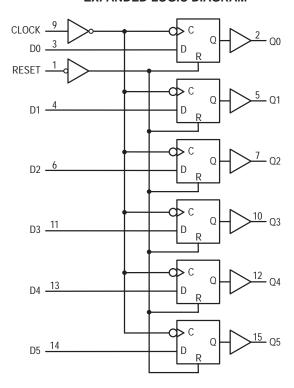
		Typical @ 25°C, V _{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Per Enabled Output)*	62	pF

^{*} Used to determine the no-load dynamic power consumption: PD = CPD VCC²f + ICC VCC. For load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

TIMING REQUIREMENTS ($C_L = 50 \text{ pF}$, Input $t_f = t_f = 6.0 \text{ ns}$)

				Guaranteed Limit						
			VCC	– 55 to	25°C	≤ 8	5°C	≤ 12	25°C	
Symbol	Parameter	Fig.	v	Min	Max	Min	Max	Min	Max	Unit
t _{Su}	Minimum Setup Time, Data to Clock	3	2.0 4.5 6.0	50 10 9.0		65 13 11		75 15 13		ns
th	Minimum Hold Time, Clock to Data	3	2.0 4.5 6.0	5.0 5.0 5.0		5.0 5.0 5.0		5.0 5.0 5.0		ns
t _{rec}	Minimum Recovery Time, Reset Inactive to Clock	2	2.0 4.5 6.0	5.0 5.0 5.0		5.0 5.0 5.0		5.0 5.0 5.0		ns
t _W	Minimum Pulse Width, Clock	1	2.0 4.5 6.0	75 15 13		95 19 16		110 22 19		ns
t _W	Minimum Pulse Width, Reset	2	2.0 4.5 6.0	75 15 13		95 19 16		110 22 19		ns
t _r , t _f	Maximum Input Rise and Fall Times	1	2.0 4.5 6.0		1000 500 400		1000 500 400		1000 500 400	ns

EXPANDED LOGIC DIAGRAM



SWITCHING WAVEFORMS

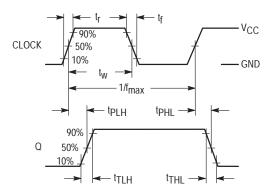


Figure 1.

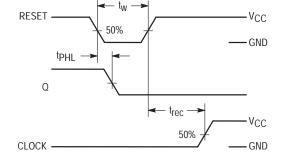
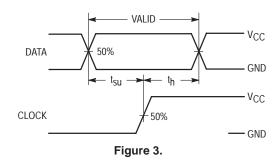
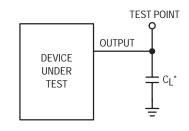


Figure 2.



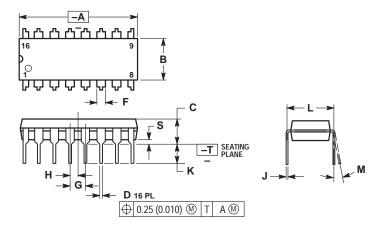


*Includes all probe and jig capacitance

Figure 4. Test Circuit

PACKAGE DIMENSIONS

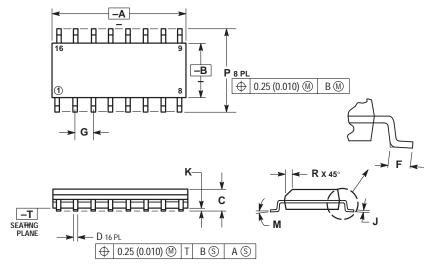
PDIP-16 **N SUFFIX** CASE 648-08 ISSUE R



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
 4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
 5. ROUNDED CORNERS OPTIONAL.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.740	0.770	18.80	19.55
В	0.250	0.270	6.35	6.85
С	0.145	0.175	3.69	4.44
D	0.015	0.021	0.39	0.53
F	0.040	0.070	1.02	1.77
G	0.	100 BSC	2	.54 BSC
Н	0.	050 BSC	1	.27 BSC
J	0.008	0.015	0.21	0.38
K	0.110	0.130	2.80	3.30
L	0.295	0.305	7.50	7.74
M	0°	10°	0°	10°
S	0.020	0.040	0.51	1.01





- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRISION.

 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- PER SIDE.
 DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.127 (0.005) TOTAL
 IN EXCESS OF THE D DIMENSION AT
 MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

Notes

Notes

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